



Excellence in Electronics

TYPE 1N432

The 1N432 is a hermetically sealed silicon junction diode designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 megohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard inline subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA

- CASE: Metal and Glass
- BASE: None (0.016" tinned dumet wire. Length: 1.0" min. Spacing: 0.080" center-to-center)
- TERMINAL CONNECTIONS: (Black Dot is adjacent to Cathode Terminal)
- MOUNTING POSITION: Any

ELECTRICAL DATA

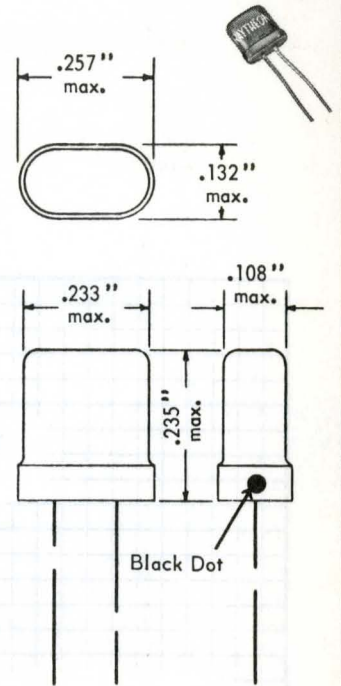
RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

Peak Inverse Voltage	40 volts
Continuous Inverse Voltage	35 volts
Average Rectified Current	60 ma.
Average Rectified Current (100°C)	40 ma.
Peak Rectified Current	120 ma.
Surge Current (for 1 sec.)	400 ma.
Ambient Temperature Range	-55 to +150 °C
Dissipations at:	
25°C	150 mw.
65°C	110 mw.
100°C	75 mw.
150°C	25 mw.

CHARACTERISTICS:

	100°C	25°C
Maximum Inverse Current at -10 volts	0.05	0.005 μa.
Minimum Forward Current at +1.0 volt		10.0 ma.

Actual Size



Tentative Data

RAYTHEON MANUFACTURING COMPANY

RECEIVING AND CATHODE RAY TUBE OPERATIONS

